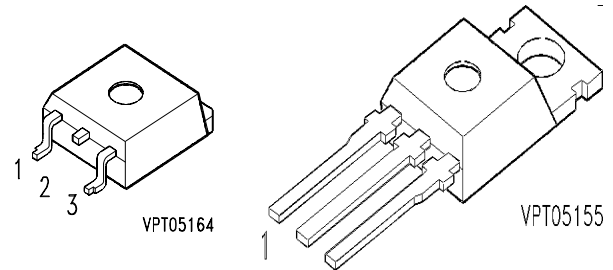


SIPMOS® Power Transistor

- N channel
- Enhancement mode
- Logic Level
- Avalanche-rated
- dv/dt rated
- 175°C operating temperature
- also in SMD available



Pin 1	Pin 2	Pin 3
G	D	S

Type	V _{DS}	I _D	R _{DS(on)}	Package	Ordering Code
BUZ111SL	55 V	80 A	0.01 Ω	TO-220 AB	Q67040-S4003-A2

Maximum Ratings

Parameter	Symbol	Values	Unit
Continuous drain current <i>T_C</i> = 100 °C	I _D	80	A
Pulsed drain current <i>T_C</i> = 25 °C	I _{Dpuls}	320	A
Avalanche energy, single pulse I _D = 80 A, V _{DD} = 25 V, R _{GS} = 25 Ω L = 220 μH, <i>T_j</i> = 25 °C	E _{AS}	700	mJ
Avalanche current, limited by <i>T_{jmax}</i>	I _{AR}	80	A
Avalanche energy, periodic limited by <i>T_{jmax}</i>	E _{AR}	25	mJ
Reverse diode dv/dt I _S = 80 A, V _{DS} = 40 V, di _F /dt = 200 A/μs <i>T_{jmax}</i> = 175 °C	dv/dt	6	kV/μs
Gate source voltage	V _{GS}	± 14	V
Power dissipation <i>T_C</i> = 25 °C	P _{tot}	250	W

Maximum Ratings

Parameter	Symbol	Values	Unit
Operating temperature	T_j	-55 ... + 175	°C
Storage temperature	T_{stg}	-55 ... + 175	
Thermal resistance, junction - case	R_{thJC}	≤ 0.6	K/W
Thermal resistance, junction - ambient	R_{thJA}	≤ 62	
IEC climatic category, DIN IEC 68-1		55 / 175 / 56	

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Static Characteristics

Drain- source breakdown voltage $V_{GS} = 0\text{ V}$, $I_D = 0.25\text{ mA}$, $T_j = 25\text{ }^\circ\text{C}$	$V_{(BR)DSS}$	55	-	-	V
Gate threshold voltage $V_{GS} = V_{DS}$, $I_D = 240\text{ }\mu\text{A}$	$V_{GS(th)}$	1.2	1.6	2	
Zero gate voltage drain current $V_{DS} = 50\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = -40\text{ }^\circ\text{C}$ $V_{DS} = 50\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 25\text{ }^\circ\text{C}$ $V_{DS} = 50\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$	I_{DSS}	-	-	0.1 1 100	μA
Gate-source leakage current $V_{GS} = 20\text{ V}$, $V_{DS} = 0\text{ V}$	I_{GSS}	-	10	100	
Drain-Source on-resistance $V_{GS} = 4.5\text{ V}$, $I_D = 80\text{ A}$ $V_{GS} = 10\text{ V}$, $I_D = 80\text{ A}$	$R_{DS(on)}$	-	0.0085 0.0055	0.01 0.007	

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

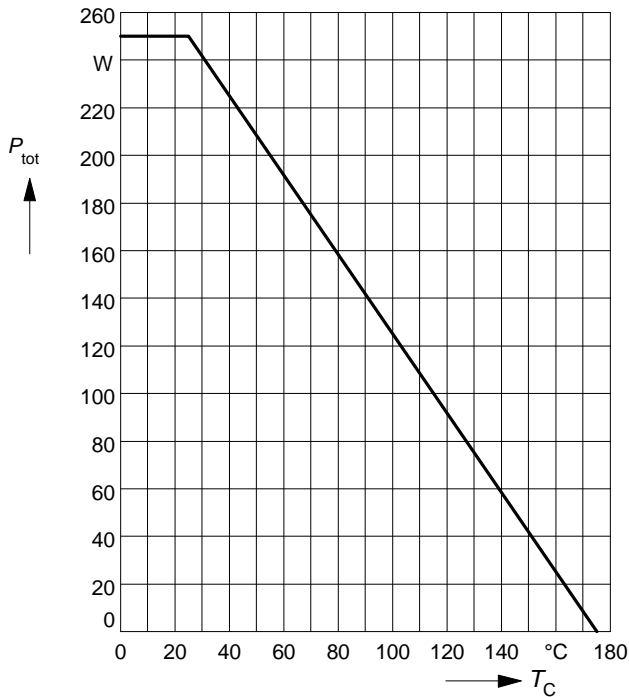
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Dynamic Characteristics					
Transconductance $V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max} = 2 \text{ V}, I_D = 80 \text{ A}$	g_{fs}	30	95	-	S
Input capacitance $V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	C_{iss}	-	3850	4800	pF
Output capacitance $V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	C_{oss}	-	1090	1357	
Reverse transfer capacitance $V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	C_{rss}	-	570	715	
Turn-on delay time $V_{DD} = 30 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 80 \text{ A}$ $R_G = 1.3 \Omega$	$t_{d(on)}$	-	30	45	ns
Rise time $V_{DD} = 30 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 80 \text{ A}$ $R_G = 1.3 \Omega$	t_r	-	37	56	
Turn-off delay time $V_{DD} = 30 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 80 \text{ A}$ $R_G = 1.3 \Omega$	$t_{d(off)}$	-	70	105	
Fall time $V_{DD} = 30 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 80 \text{ A}$ $R_G = 1.3 \Omega$	t_f	-	36	55	
Gate charge at threshold $V_{DD} = 40 \text{ V}, I_D \geq 0.1 \text{ A}, V_{GS} = 0 \text{ to } 1 \text{ V}$	$Q_{g(th)}$	-	3.8	5.7	nC
Gate charge at 5.0 V $V_{DD} = 40 \text{ V}, I_D = 80 \text{ A}, V_{GS} = 0 \text{ to } 5 \text{ V}$	$Q_{g(5)}$	-	92	138	
Gate charge total $V_{DD} = 40 \text{ V}, I_D = 80 \text{ A}, V_{GS} = 0 \text{ to } 10 \text{ V}$	$Q_{g(total)}$	-	155	232	
Gate plateau voltage $V_{DD} = 40 \text{ V}, I_D = 80 \text{ A}$	$V_{(plateau)}$	-	3.4	-	V

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Reverse Diode					
Inverse diode continuous forward current $T_C = 25^\circ\text{C}$	I_S	-	-	80	A
Inverse diode direct current, pulsed $T_C = 25^\circ\text{C}$	I_{SM}	-	-	320	
Inverse diode forward voltage $V_{GS} = 0\text{ V}, I_F = 160\text{ A}$	V_{SD}	-	1.25	1.8	V
Reverse recovery time $V_R = 30\text{ V}, I_F = I_S, di_F/dt = 100\text{ A}/\mu\text{s}$	t_{rr}	-	105	157	ns
Reverse recovery charge $V_R = 30\text{ V}, I_F = I_S, di_F/dt = 100\text{ A}/\mu\text{s}$	Q_{rr}	-	0.31	0.47	μC

Power dissipation

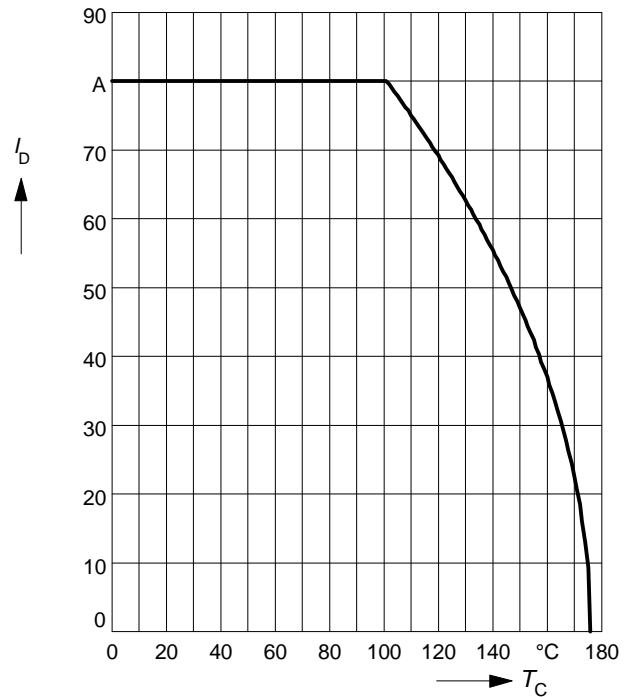
$$P_{\text{tot}} = f(T_C)$$



Drain current

$$I_D = f(T_C)$$

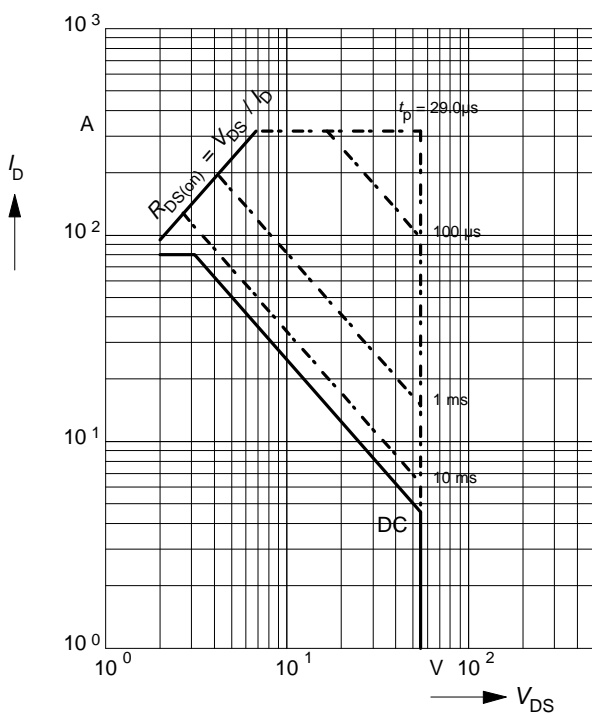
parameter: $V_{GS} \geq 4 \text{ V}$



Safe operating area

$$I_D = f(V_{DS})$$

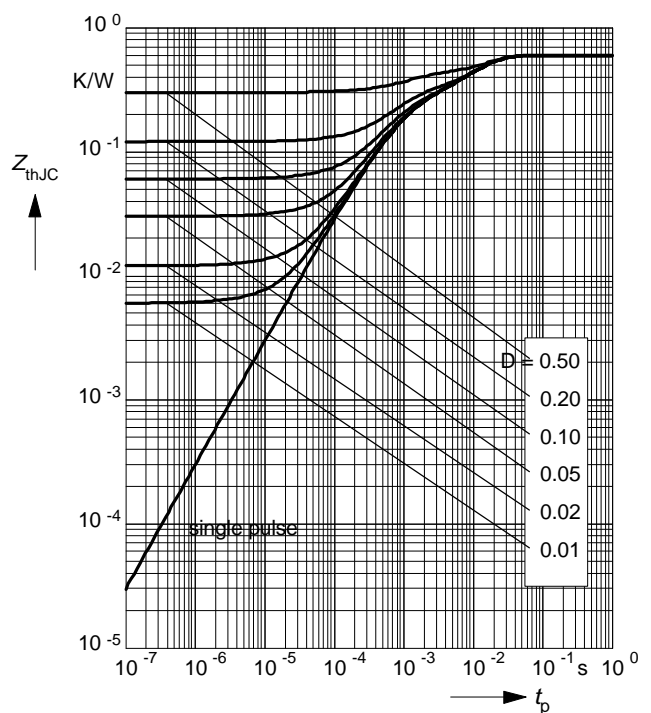
parameter: $D = 0, T_C = 25^\circ\text{C}$



Transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

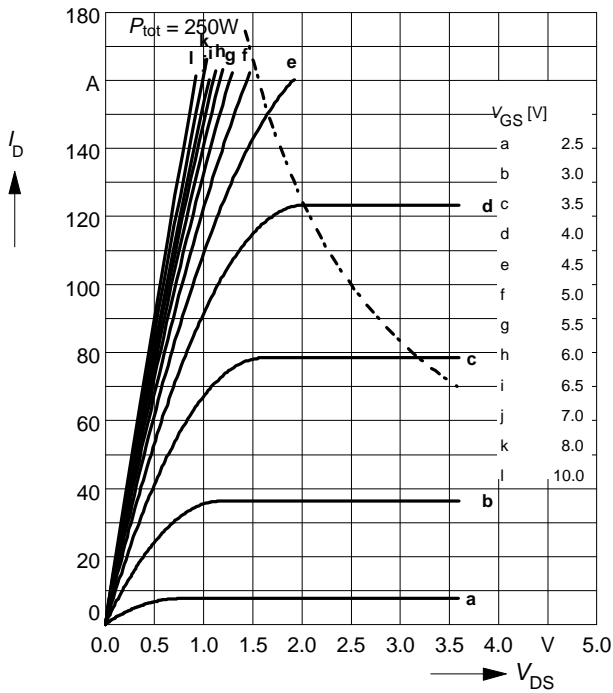
parameter: $D = t_p / T$



Typ. output characteristics

$$I_D = f(V_{DS})$$

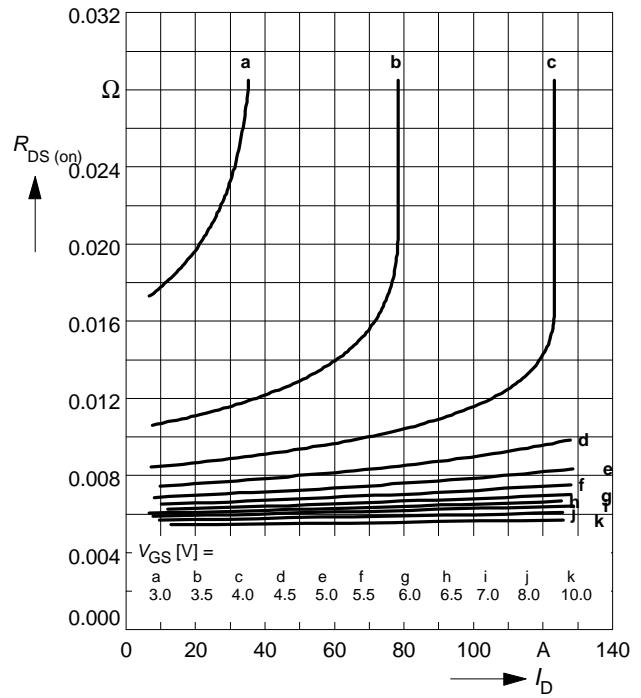
parameter: $t_p = 80 \mu s$



Typ. drain-source on-resistance

$$R_{DS(on)} = f(I_D)$$

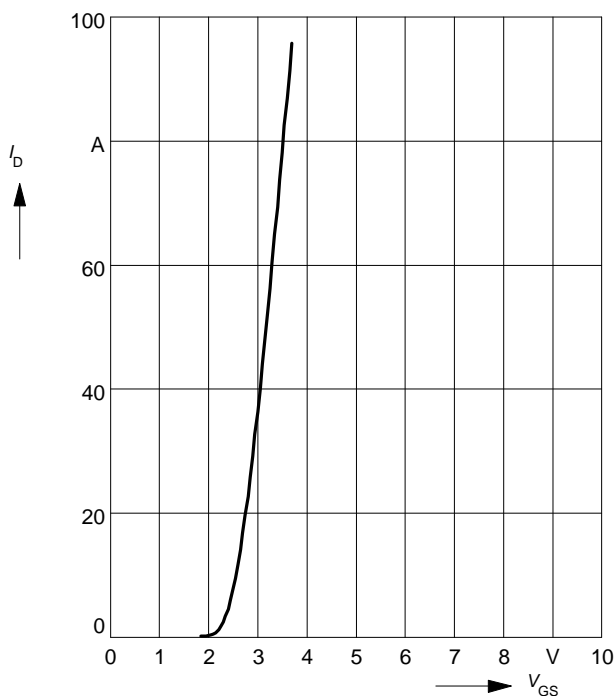
parameter: $t_p = 80 \mu s, T_j = 25^\circ C$



Typ. transfer characteristics $I_D = f(V_{GS})$

parameter: $t_p = 80 \mu s$

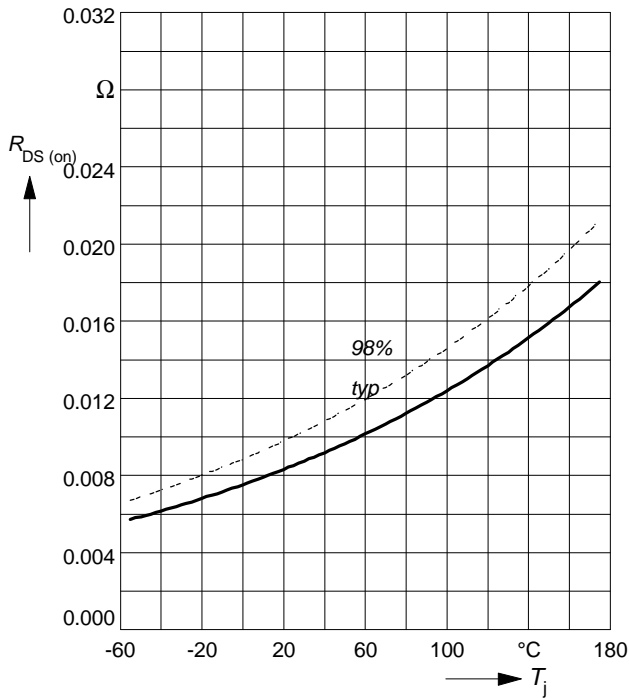
$$V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$



Drain-source on-resistance

$$R_{DS(on)} = f(T_j)$$

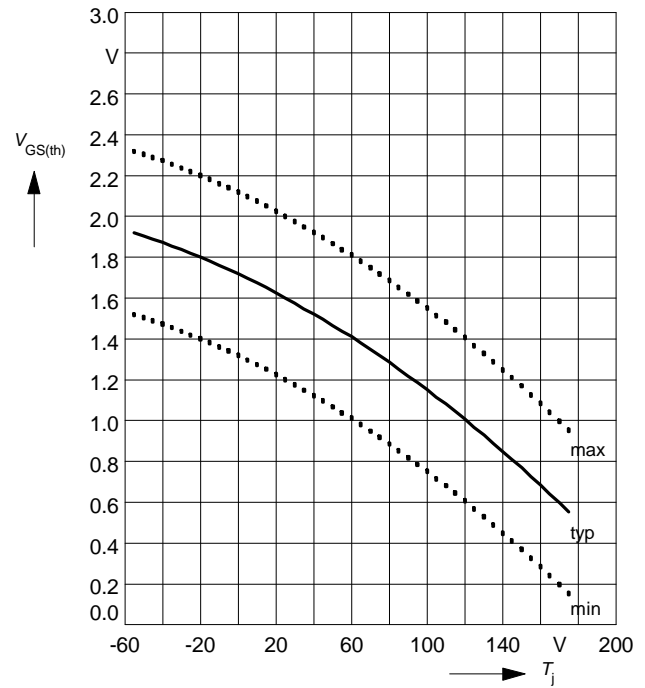
parameter: $I_D = 80 \text{ A}$, $V_{GS} = 4.5 \text{ V}$



Gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

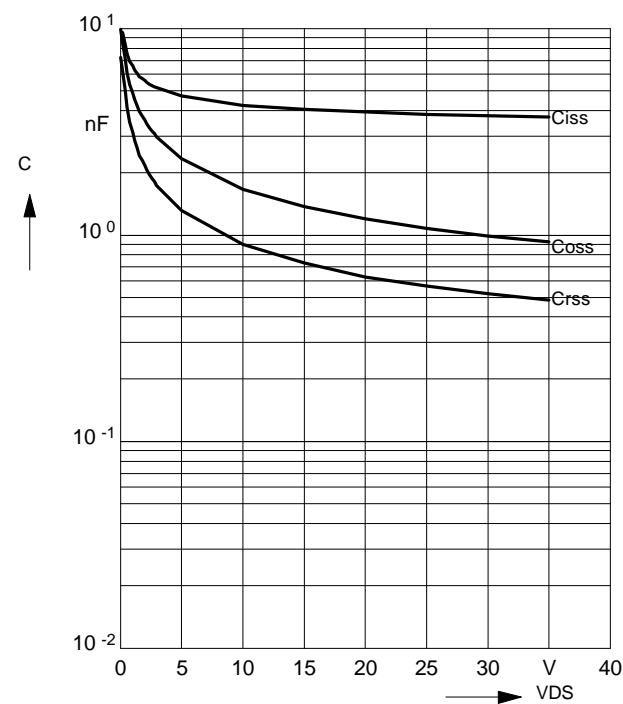
parameter: $V_{GS} = V_{DS}$, $I_D = 240 \mu\text{A}$



Typ. capacitances

$$C = f(V_{DS})$$

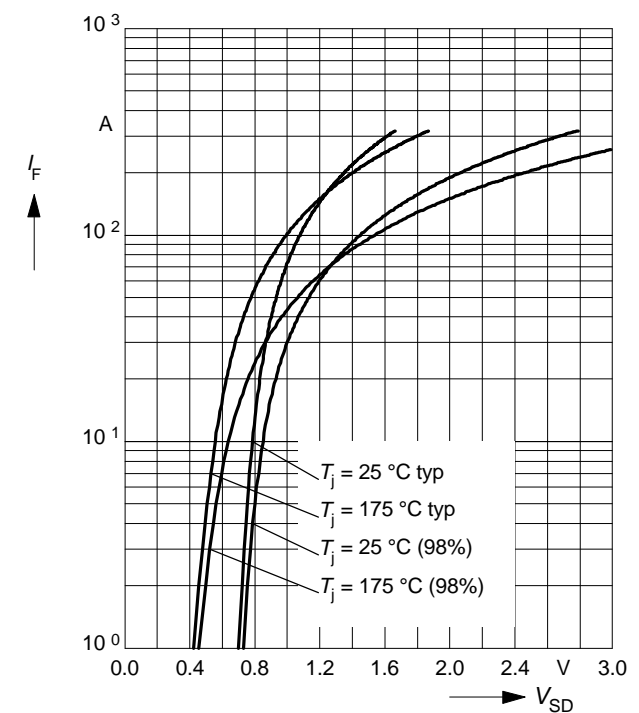
parameter: $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$



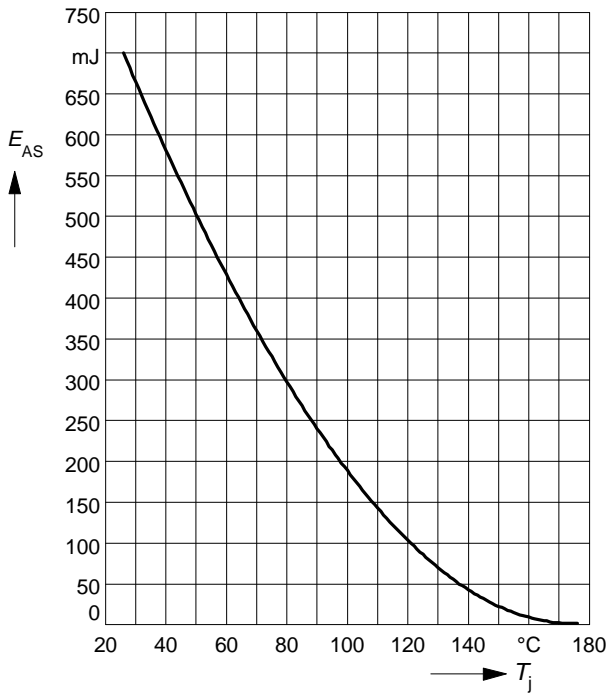
Forward characteristics of reverse diode

$$I_F = f(V_{SD})$$

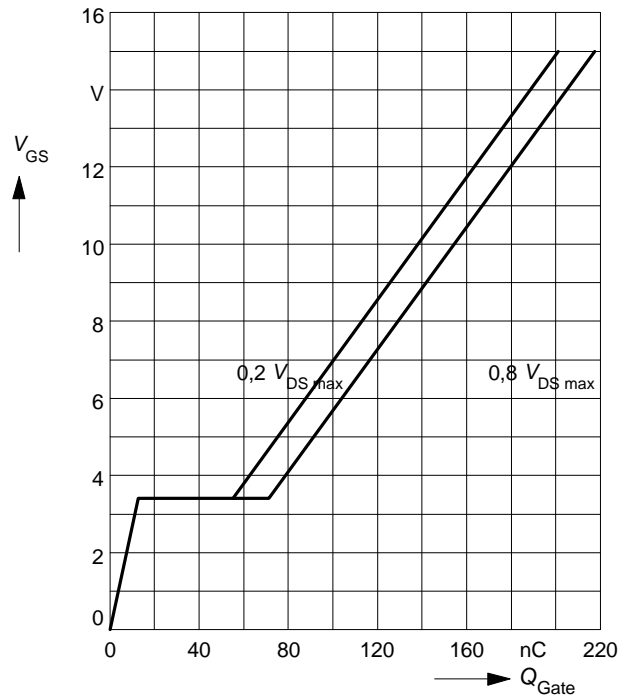
parameter: T_j , $t_p = 80 \mu\text{s}$



Avalanche energy $E_{AS} = f(T_j)$
 parameter: $I_D = 80 \text{ A}$, $V_{DD} = 25 \text{ V}$
 $R_{GS} = 25 \Omega$, $L = 220 \mu\text{H}$



Typ. gate charge
 $V_{GS} = f(Q_{Gate})$
 parameter: $I_{D \text{ puls}} = 80 \text{ A}$



Drain-source breakdown voltage

$V_{(BR)DSS} = f(T_j)$

